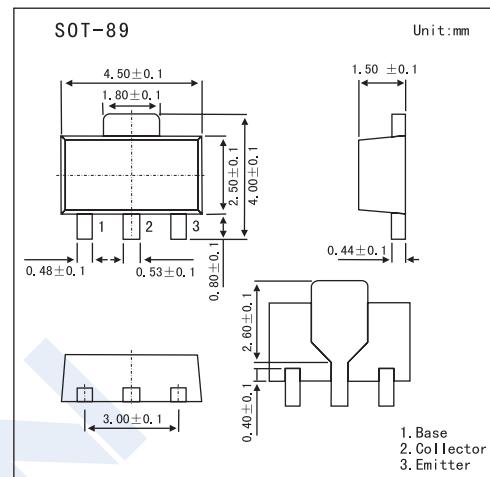


Digital Transistors

HR1A4M

■ Features

- Up to 2A High Current Drives Such As IC Outputs and
Actuators Available
- On-chip Bias Resistor
- Low Power Consumption During Drive



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-10	V
Collector Current (DC)	I _{C(DC)}	-1.0	A
Collector Current (Pulse)	I _{C(pulse)} *1	-2.0	A
Base Current (DC)	I _{B(DC)}	-0.02	A
Total Power Dissipation	P _T *2	2.0	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1 PW ≤ 10ms, Duty Cycle ≤ 50%

*2 When 0.7mm x 16cm² ceramic board is used.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} = -60V, I _E = 0			-100	nA
DC Current Gain	h _{FE} *	V _{CE} = -2.0V , I _C = -0.1A	150			
		V _{CE} = -2.0V , I _C = -0.5A	100			
		V _{CE} = -2.0V , I _C = -1.0A	50			
Low Level Output Voltage	V _{OL} *	V _{IN} = -5.0V, I _C = -0.1A			-0.2	V
Low Level Input Voltage	V _{IL} *	V _{CE} = -5.0V, I _C = -100 μ A			-0.3	V
Input Resistance	R ₁		7	10	13	kΩ
Emitter-Base Resistance	R ₂		7	10	13	kΩ

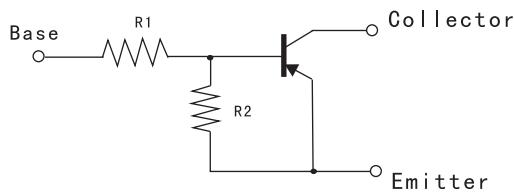
* PW ≤ 350 μ s, Duty Cycle ≤ 2%

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■ Marking

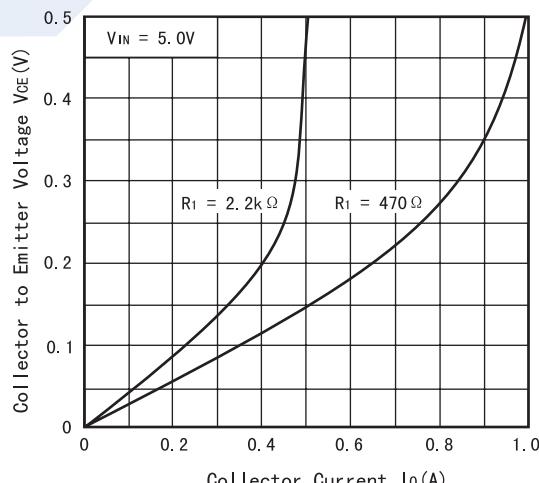
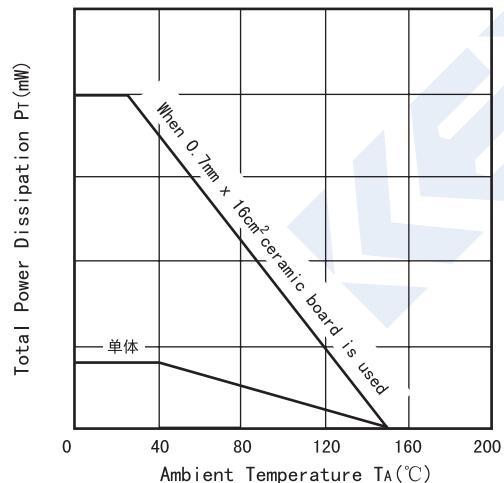
Marking	MS
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■ Equivalent Circuit



$R_1 = 10\text{ k}\Omega$ $R_2 = 10\text{ k}\Omega$

■ Electrical Characteristics Curves



HR1A4M